

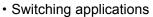
# Isc N-Channel MOSFET Transistor

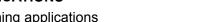
## IPA65R420CFD

#### • FEATURES

- With TO-220F Package
- · Drain Source Voltage-
  - : V<sub>DSS</sub>=650V(Min)
- Static Drain-Source On-Resistance
  - :  $R_{DS(on)} = 0.42 \Omega (Max)$
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation





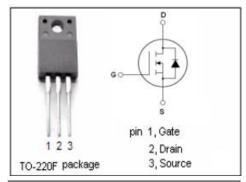


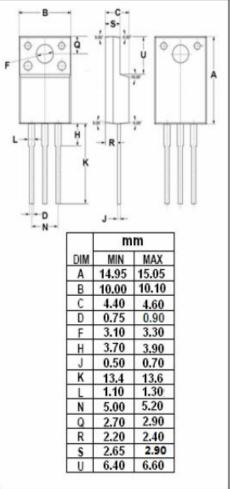
## ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	650	V
V <sub>GSS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous @Tc=25°C (V <sub>GS</sub> at 10V) Tc=100°C	8.7 5.5	А
I <sub>DM</sub>	Drain Current-Single Pulsed	27	Α
P <sub>D</sub>	Total Dissipation @T <sub>c</sub> =25℃	31.2	W
Tj	Max. Operating Junction Temperature	-55~150	$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	4	°C/W
Rth(ch-a)	Channel-to-ambient thermal resistance	80	°C/W





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## **Isc N-Channel MOSFET Transistor**

## IPA65R420CFD

#### ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =1mA	650			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =0.3mA	3.5	4	4.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =4.4A		0.378	0.42	Ω
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V			±100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0V;Tj=25°C V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0V; Tj=150°C		100	1	μ <b>A</b>
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =5.2A, V <sub>GS</sub> = 0 V		0.9		V



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